Ultra-Low Voltage Operation Omnipolar Detection Type Hall Effect Switch IC

General Description

The ET3725B30 is a high sensitivity and high-accuracy Omnipolar Hall effect switch IC that operates at an ultra-low voltage and low current consumption. ET3725B30 has two CMOS output terminal for N and S pole. The output voltage will be pulled low when this IC detects the magnetic flux density is larger than operate point(B_{OPN}/B_{OPS}) and the output voltage will recover to high until the magnetic flux density is smaller than the release point(B_{RPN}/B_{RPS}). Using this IC with a magnet makes it possible to detect the open / close status in various applications.

To achieve a high-density mounting the ET3725B30 uses a super-small DFN4 package.

The ET3725B30 is suitable for battery powered portable devices such as mobile phones and portable PCs etc. due to its low voltage operation and low current consumption, the average current consumption is only typ. 2.0μA with a 1.2V supply.

Features

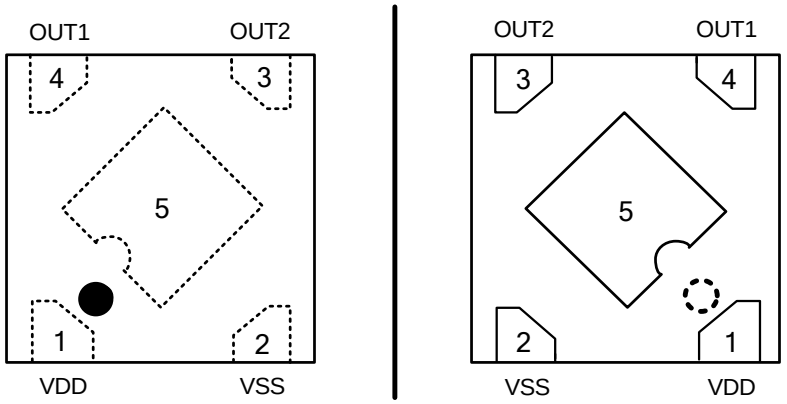
- Pole detection：Omnipolar pole
- Output logic：Dual active low output for N/S-pole
- Output form：CMOS output, no external pull-up resistor required
- Operating Point：B_{OP} = 3.0 mT typ.
- Operating cycle：t_{CYCLE} = 50 ms typ.
- Current consumption：I_{DD} = typ. 2.0 μA at 1.2 V
- Power supply voltage range：V_{DD} = 1.0 V to 3.5 V
- Operation temperature range：T_A = -40°C to +85°C
- Lead-free (Sn 100%), halogen-free
- Product name and packaging form:

Part No.	Package	Packing Option	MSL
ET3725B30	DFN4(1.0mm×1.0mm)	Tape and reel, 10K/Reel	1

Application

- Open/Close detection for flip mobile phones
- Smart cover for smart phones
- Smart cover for portable PCs, tablet PCs
- Digital video cameras and portable game consoles
- Home appliances

Pin Configuration



TOP VIEW BOTTOM VIEW

Pin Function

Pin No.	Pin Name	Pin Function
1	VDD	Power supply pin
2	VSS	Ground Pin
3	OUT2	S Pole Detection Output pin
4	OUT1	N Pole Detection Output pin
5	Thermal Pad	Leave floating

Block Diagram

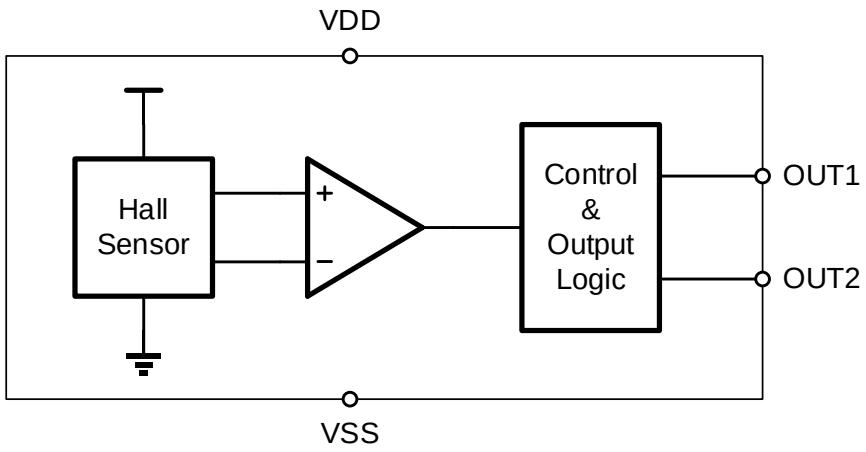


Figure 1. Block Diagram

Functional Description

Applied magnetic flux

The magnetic flux applied to ET3725B30 should on the vertical direction on marking surface. If not, the horizontal component has no effect to detection. ET3725B30 is omnipolar type detector, the corresponding output voltage is inverted when the sufficient S or N type magnetic flux is applied to IC.

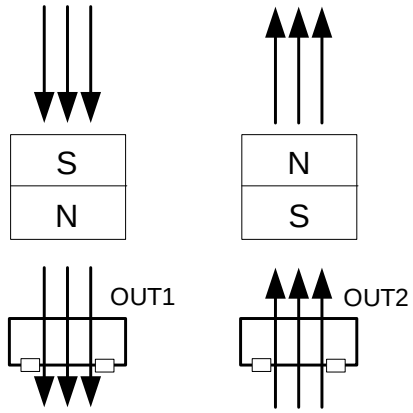


Figure 2. Magnetic Flux Direction

Hall sensor Position

The Hall sensor embedded in ET3725B30 is at the center of IC. As show below, the position of this Hall sensor is located in the area indicated by a circle, the diameter size of which is about 0.3 mm.

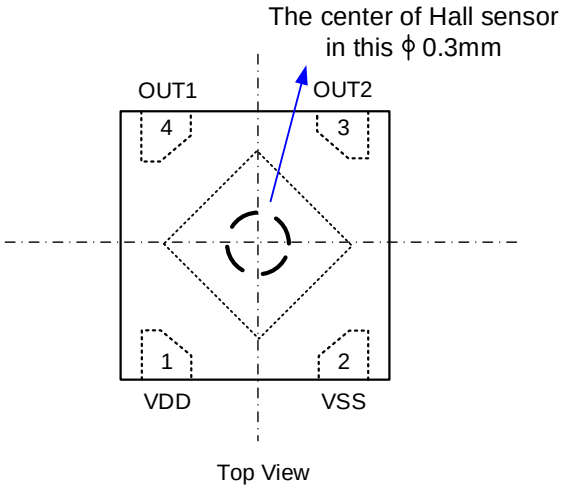


Figure 3. Hall Sensor Position

Detecting Operation

ET3725B30 detects magnetic field periodically. When vertical component of the magnetic flux applied to IC exceeds the operating point (B_{OPN} or B_{OPS}) such as the S or N pole of a magnet is moved closer to IC, V_{OUT} changes from "H" to "L". On the contrary, if magnetic flux is lower than the release point (B_{RPN} or B_{RPS}), V_{OUT} changes from "L" to "H".

The relationship between the magnetic flux density and V_{OUT} is shown below.

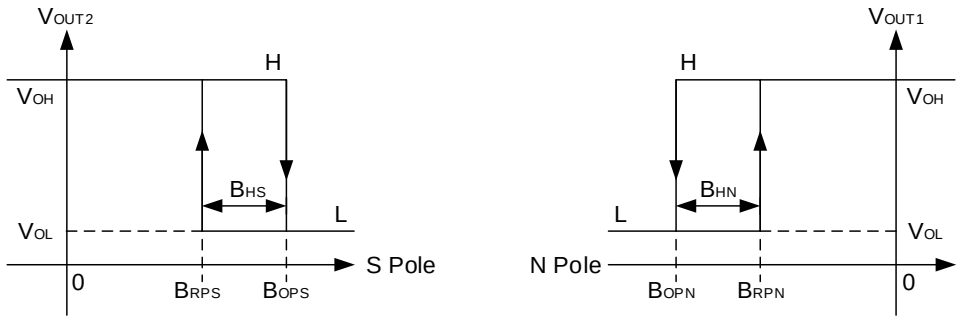


Figure 4. Magnetic Flux Density vs VOUT

Operating Current

ET3725B30 performs the intermittent operation, therefore the average current consumption depends on the current in active mode , the active period (t_{AW}), the current in sleep mode, and sleep period(t_{SL}). The active current is about 640 μA typically, and 0.72 μA at sleep mode. Please refer to electrical characteristic table for detail.

The time dependency of the current consumption is shown below.

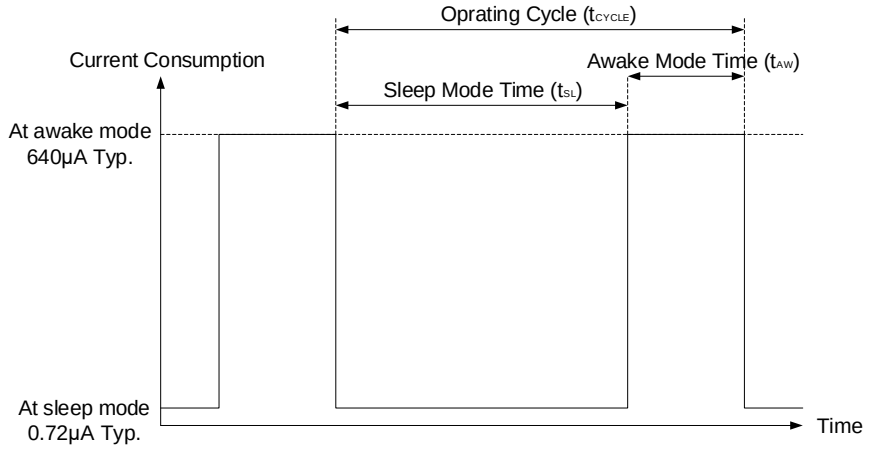


Figure 5. Operating Current

Timing Diagram

The operation timing of this IC is shown below.

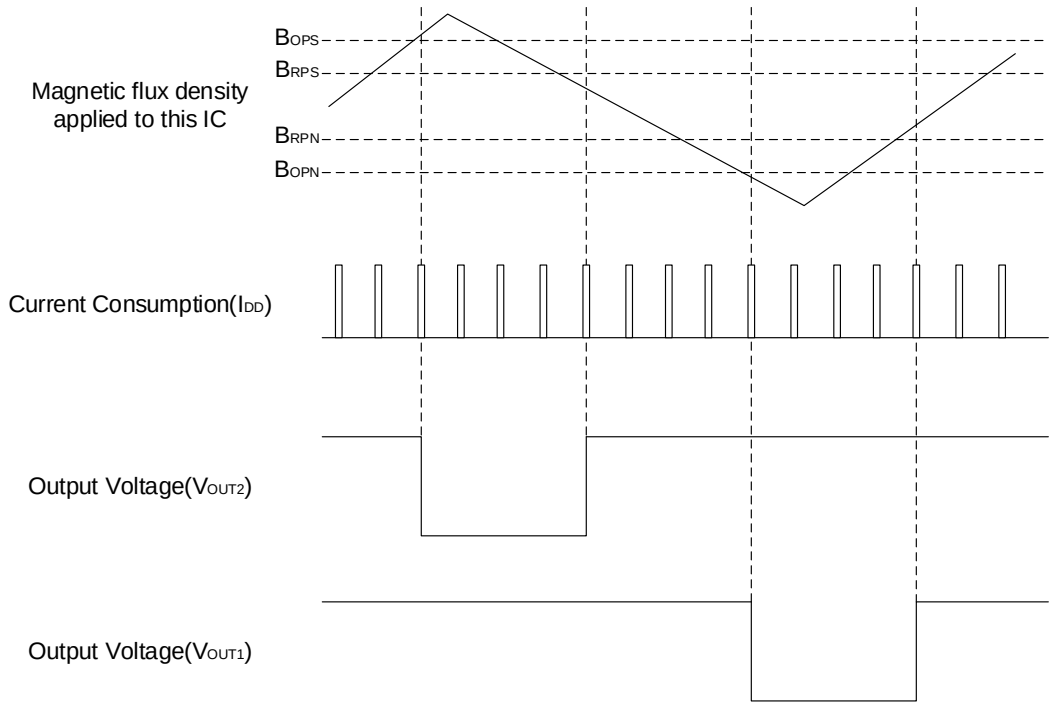


Figure 6. Timing Diagram

Absolute Maximum Ratings

(T_A = +25°C unless otherwise specified)

Symbol	Parameters	Rating	Unit
V_{DD}	Power supply voltage	V_{SS}-0.3 ~ V_{SS}+4.5	V
I_{OUT}	Output current	±1.0	mA
V_{OUT}	Output voltage	V_{SS} − 0.3 ~ V_{DD} + 0.3	V
T_A	Operation ambient temperature	−40 ~ +85	°C
T_{STG}	Storage temperature	−40 ~ +125	°C
θ_{JA}	Junction-to-ambient thermal resistance	250	°C/W

Note: The absolute maximum ratings are rated values exceeding which the product could suffer physical damage. These values must therefore not be exceeded under any conditions.

Electrical Characteristics

(T_A = +25°C, V_{DD} = 1.2 V, unless otherwise specified)

Symbol	Parameters	Conditions		Min	Typ	Max	Unit
V_{DD}	Power supply voltage	-		1.0	1.2	3.5	V
I_{DD}	Current consumption	Average Supply Current	V_{DD}=1.2V	-	2.0	3.5	μA
			V_{DD}=1.8V	-	2.5	4.0	
V_{OL}	Output voltage	CMOS output OUT1,OUT2	I_{OUT} = 0.5mA	-	-	0.4	V
V_{OH}			I_{OUT} = −0.5mA	V_{DD}-0.4	-	-	V
t_{AW}	Awake mode time	-		-	0.10	-	ms
t_{SL}	Sleep mode time	-		-	50.0	-	ms
t_{CYCLE}	Operating cycle	t_{AW} + t_{SL}		-	50.0	100.0	ms

Magnetic Characteristics

(T_A = +25°C, V_{DD} = 1.2 V, unless otherwise specified)

Parameters		Symbol	Conditions	Min	Typ	Max	Unit
Operation point[(1)]	S pole	B_{OPS}		1.4	3.0	4.0	mT[(4)]
	N pole	B_{OPN}		-4.0	-3.0	-1.4	mT
Release point[(2)]	S pole	B_{RPS}		1.1	2.2	3.7	mT
	N pole	B_{RPN}		-3.7	-2.2	-1.1	mT
Hysteresis width[(3)]	S pole	B_{HS}	$B_{HS} = B_{OPS} - B_{RPS}$		0.8		mT
	N pole	B_{HN}	$B_{HN} = \lvert B_{OPN} - B_{RPN} \rvert$		0.8		mT

Notes:

(1) Operating points (B_{OPN}, B_{OPS}): B_{OPN} and B_{OPS} are the values of magnetic flux density triggers the output voltage (V_{OUT}) to low by increasing the N pole or S pole magnetic flux density applied to this IC. Even when the magnetic flux density is larger than B_{OPN} or B_{OPS}, V_{OUT} status is held.

(2) Release points (B_{RPN}, B_{RPS}): B_{RPN} and B_{RPS} are the values of magnetic flux density makes the output voltage (V_{OUT}) recover to high by decreasing the N pole or S pole magnetic flux density applied to this IC. Even when the magnetic flux density is lower than B_{RPN} or B_{RPS}, V_{OUT} status is held.

(3) Hysteresis widths (B_{HN}, B_{HS}): B_{HN} and B_{HS} are the difference between B_{OPN} and B_{RPN}, and B_{OPS} and B_{RPS}, respectively.

(4) The unit of magnetic density mT can be converted by using the formula 1 mT = 10 Gauss.

Application Circuit

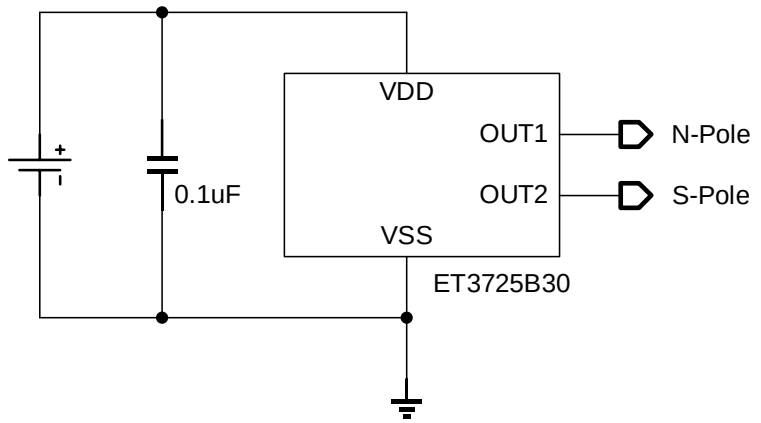
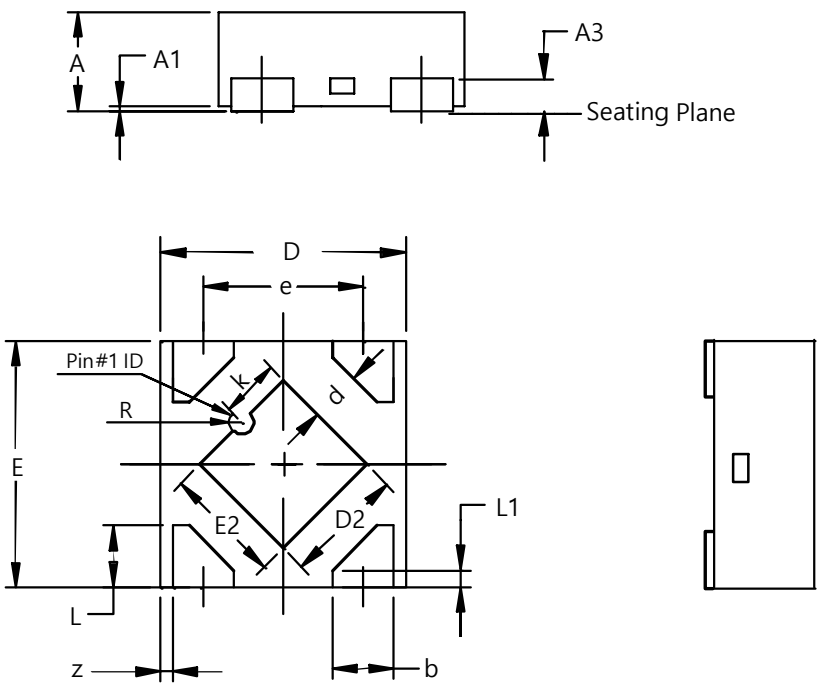


Figure 7. Application Circuit

Precautions

- The power supply for this IC should has low impedance, the IC may malfunction due to a supply voltage drop caused by feed through current.
- Power supply voltage rapidly changing may cause IC malfunction.
- Large stress on this IC may affect the magnetic characteristics. Avoid large stress applied to the IC on a board.
- Thermal pad need floating .

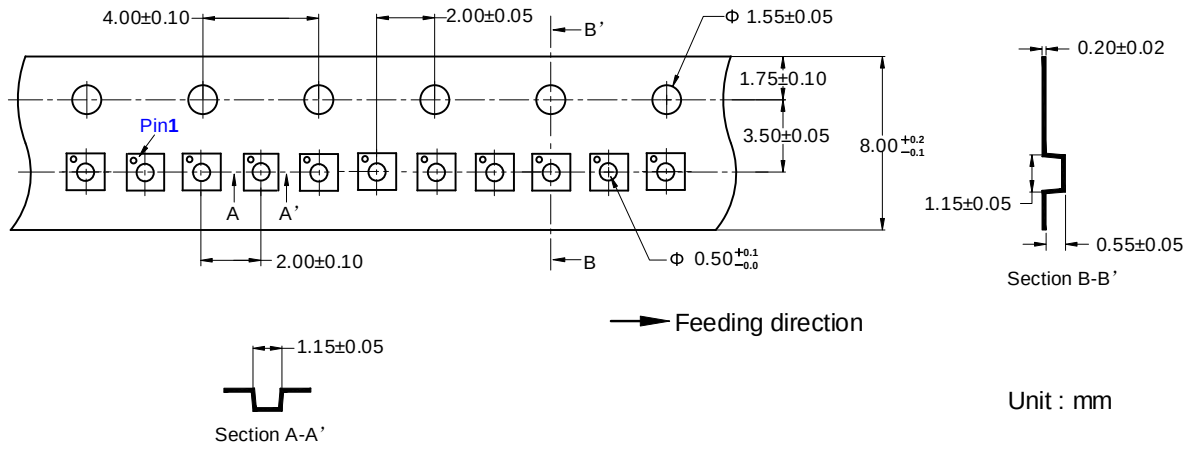
Package Dimension



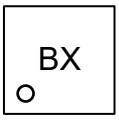
COMMON DIMENSIONS
(UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	NOM	MAX
A	0.3	0.38	0.40
A1	0.00	0.03	0.05
A3		0.127REF	
b	0.20	0.25	0.30
D	0.95	1.00	1.05
D2	0.43	0.48	0.53
E	0.95	1.00	1.05
E2	0.43	0.48	0.53
d	-	0.205	-
e		0.65BSC	
k	0.19	0.24	0.29
L	0.15	0.25	0.35
L1	0.02	0.07	0.12
R	0.02	0.05	0.08
z	-	0.050	-

Tape Information



Marking



B - Part Number

X - Tracking Number

Note: X (Tracking Number) is variable, according to the wafer lot number

Revision History and Checking Table

Version	Date	Revision Item	Modifier	Function & Spec Checking	Package & Tape Checking
1.0	2026.3.13	Original Version	Zhangy	Wanggp	Liujy